

PNP -0.7A -80V Middle Power Transistor

Parameter	Value
V_{CEO}	-80V
I _C	-0.7A

Features

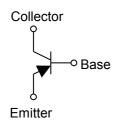
- 1) Suitable for Middle Power Driver
- 2) Complementary NPN Types: 2SCR514P
- 3) Low V_{CE(sat)}

$$V_{CE(sat)} = -0.4V(Max.)$$

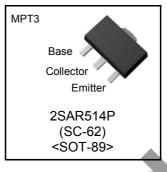
 $(I_C/I_B = -300mA/-15mA)$

4) Lead Free/RoHS Compliant.

•Inner circuit



Outline



Applications

Motor driver , LED driver Power supply

Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
2SAR514P	MPT3	4540	T100	180	12	1,000	MD

● Absolute maximum ratings (Ta = 25°C)

Parameter		Values	Unit
Collector-base voltage		-80	V
Collector-emitter voltage		-80	V
Emitter-base voltage		-6	V
DC	I _C	-0.7	А
Pulsed	I _{CP} *1	-1.4	А
Power dissipation		0.5	W
		2.0	W
Junction temperature		150	°C
Range of storage temperature		−55 to +150	°C
	DC Pulsed	$\begin{array}{c c} & V_{CBO} \\ \hline & V_{CEO} \\ \hline & V_{EBO} \\ \hline \\ DC & I_C \\ \hline Pulsed & I_{CP}^{*1} \\ \hline & P_D^{*2} \\ \hline & P_D^{*3} \\ \hline & T_j \\ \hline \end{array}$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

^{*1} Pw=10ms, single pulse

^{*2} Each terminal mounted on a reference land

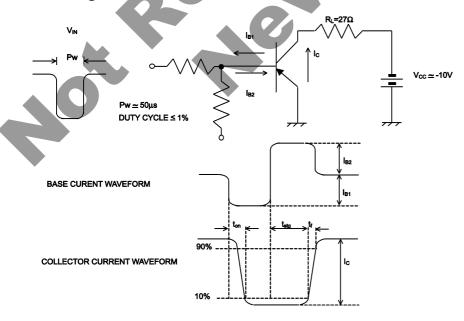
^{*3} Mounted on a ceramic board (40×40×0.7mm)

●Electrical characteristics(Ta = 25°C)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-emitter breakdown voltage	BV _{CEO}	I _C = -1mA	-80	-	-	V
Collector-base breakdown voltage	BV _{CBO}	$I_{C} = -100 \mu A$	-80	-	-	V
Emitter-base breakdown voltage	BV _{EBO}	$I_E = -100 \mu A$	-6	ı	-	V
Collector cut-off current	I _{CBO}	V _{CB} = -80V	ı	-	1	μА
Emitter cut-off current	I _{EBO}	V _{EB} = -4V	-	-	-1	μΑ
Collector-emitter saturation voltage	V _{CE(sat)} *1	$I_C = -300 \text{mA}, I_B = -15 \text{mA}$		-0.20	-0.40	V
DC current gain	h _{FE}	$V_{CE} = -3V$, $I_{C} = -100$ mA	120	-	390	-
Transition frequency	f _⊤	$V_{CE} = -10V, I_{E} = -200 \text{mA}$ f=100MH _Z	-	380	-	MHz
Output capacitance	C _{ob}	$V_{CB} = -10V, I_{E} = 0A,$ f = 1MHz	-	10	-	pF
Turn-on time	t _{on} *2	I _C = -0.35A	C	50	-	ns
Storage time	t _{stg} *2	I _{B1} = -35mA I _{B2} =35mA	-	350	-	ns
Fall time	t _f *2	V _{CC} [≃] −10V	-	50	-	ns

^{*1} Pulsed

•Switching time test circuit



^{*2} See switching time test circuit

●Electrical characteristic curves(Ta = 25°C)

Fig.1 Ground Emitter Propagation Characteristics

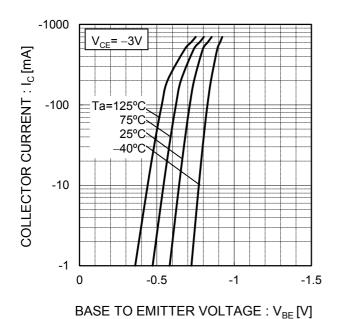
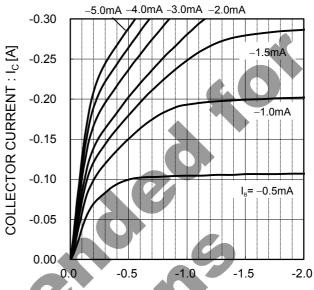


Fig.2 Typical Output Characteristics



COLECTOR TO EMITTE VOLTAGE : V_{CE} [V]

Fig.3 DC Current Gain vs. Collector Current(I)

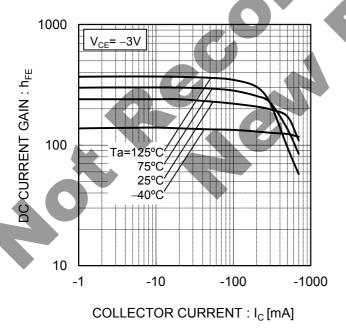
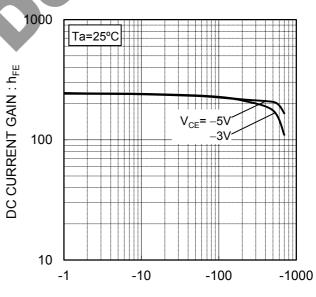


Fig.4 DC current gain vs. output current (II)



COLLECTOR CURRENT : I_C [mA]

●Electrical characteristic curves(Ta = 25°C)

Fig.5 Collector-Emitter Saturation Voltage

COLLECTOR CURRENT : I_C [mA]

vs. Collector Current (II)

Ta=25°C

Ta=25°C

Ta=25°C

To Ta=25°C

Fig.6 Collector-Emitter Saturation Voltage

Fig.7 Base-Emitter Saturation Voltage vs. Collector Current -10 $I_{\rm C}/I_{\rm B}=20$ BASE-EMITTER SATURATION VOLTAGE : V_{BE(sat)} [V] Pulsed -40°C 25°C 75°C 125°C -0.1 -1 -10 -100 -1000 COLLECTOR CURRENT: Ic [mA]

Fig.8 Gain Bandwidth Product
vs. Emitter Current

1000

Ta=25°C
V_{CE}= -10V

10

10

10

To
1000

EMITTER CURRENT: I_E [mA]

●Electrical characteristic curves(Ta = 25°C)

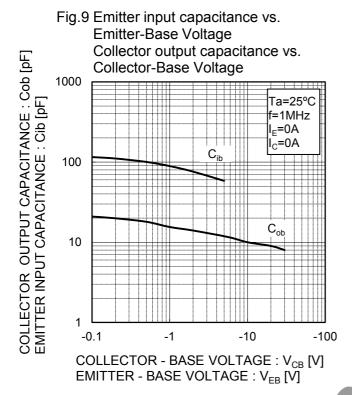
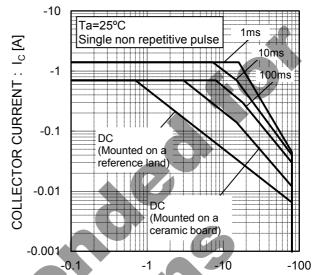


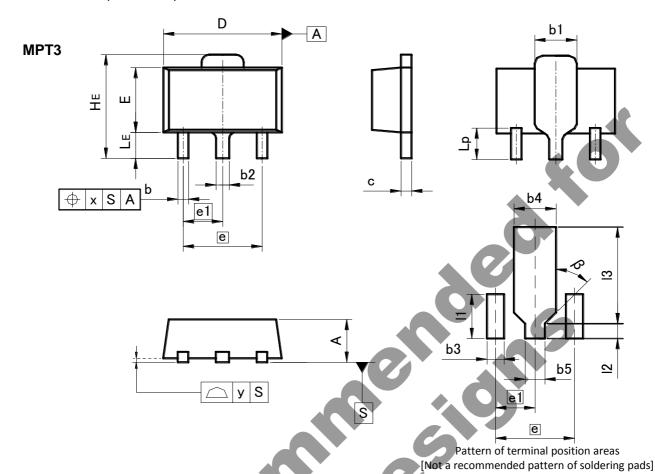
Fig.10 Safe Operating Area



COLLECTOR TO EMITTER VOLTAGE : V_{CE} [V]



●Dimensions (Unit: mm)



		·			
DIM	MILIM	ETERS	INCHES		
DIIVI	MIN	MAX	MIN	MAX	
Α	1.40	1.50	0.055	0.059	
b	0.30	0.50	0.012	0.020	
b1	1.50	1.70	0.059	0.067	
b2	0.40	0.60	0.016	0.024	
C	0.35	0.50	0.014	0.020	
D	4.40	4.70	0.173	0.185	
E	2.40	2.70	0.094	0.106	
е	3.0	00	0.118		
e1	1.	50	0.059		
HE	3.70	4.30	0.146	0.169	
LE	0.80	1.20	0.031	0.047	
Lp	1.01	1.41	0.040	0.056	
Х	ı	0.15	1	0.006	
У		0.10	-	0.004	

DIM	MILIM	ETERS	INCHES		
	MIN	MAX	MIN	MAX	
b3	-	0.65	ı	0.026	
b4	_	1.70	-	0.067	
b5		0.75	I	0.030	
l1	_	1.71	I	0.067	
12	_	0.58	I	0.023	
13	_	3.72	-	0.146	
β	45°		45	0	

Dimension in mm / inches

Notes

- 1) The information contained herein is subject to change without notice.
- Before you use our Products, please contact our sales representative and verify the latest specifications:
- 3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors.

 Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM.
- 4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.
- 5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.
- 6) The Products are intended for use in general electronic equipment (i.e. AV/OA devices, communication, consumer systems, gaming/entertainment sets) as well as the applications indicated in this document.
- 7) The Products specified in this document are not designed to be radiation tolerant.
- 8) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative: transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.
- Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.
- 10) ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.
- 11) ROHM has used reasonable care to ensur the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.
- 12) Please use the Products in accordance with any applicable environmental laws and regulations, such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.
- 13) When providing our Products and technologies contained in this document to other countries, you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.
- 14) This document, in part or in whole, may not be reprinted or reproduced without prior consent of ROHM.



Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ROHM Semiconductor: 2SAR514PT100